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Karen Cinq-Mars 3/23/04  
(Signature & date)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of : March 23, 2004  
Tze-Chiang Chen, et al. : Group Art Unit: to be assigned  
Serial No. to be assigned : Examiner: to be assigned  
Filed: 3/23/04 : International Business Machines Corporation  
2070 Route 52  
Hopewell Junction, NY 12533

**TITLE:** BILAYER HDP CVD/PE CVD CAP IN ADVANCED BEOL INTERCONNECT STRUCTURES  
AND METHOD THEREOF

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,  
Tze-Chiang Chen, et al.

By Margaret A. Pepper  
Margaret A. Pepper  
Registration No. 45,008  
Telephone No. 845-894-4713

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. <b>FIS9-2001-029 5US3</b>		SERIAL NO. <b>10/047,964</b>	
				Tze-Chiang Chen et al.			
				FILING <b>01/15/2002</b>		GROUP	

  

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,043,152	03/28/2000	Chang et al.			
		6,080,529	06/27/2000	Ye et al.			
		6,099,701	08/08/2000	Liu et al.			
		6,107,188	08/22/2000	Liu et al.			
		6,127,238	10/03/2000	Liao et al.			
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		6,211,061 B1	04/03/2001	Chen et al.			
		6,218,732 B1	04/17/2001	Russell et al.			
		6,225,210 B1	05/01/2001	Ngo et al.			
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*	EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
		WO 00/19523	06/06/2000	CA,CN,JP, European Patent				
		JP2001015480A	01/19/2001	Japan				
		JP2001053076A	02/23/2001	Japan				
		JP1111843A	04/28/1989	Japan				
		WO 99/33102	07/01/1999	JP,KR, European Patent				

  

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>			
*	EXAMINER INITIAL		Soo Geun Lee et al., "Low Dielectric Constant 3MS a-SiC:H as Cu Diffusion Barrier Layer in Cu Dual Damascene Process," Japanese Journal of Applied Physics, Part 1, Vol. 40, No. 4B, pp. 2663-2668, April 2001.
			R.D. Goldblatt et al., "A High Performance 0.13 um Copper BEOL Technology with Low-k Dielectric," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 261-263, June 5-7, 2000.

  

EXAMINER	DATE CONSIDERED
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

ATTY DOCKET NO.  
FIS9-2001-0295US3

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10/047,964

Tze-Chiang Chen et al.

FILING  
01/15/2002

GROUP

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,261,951 B1	07/17/2001	Buchwalter et al.			
	US 2001/0000155 A1	04/05/2001	Huang et al.			
	US 2001/0002333 A1	05/31/2001	Huang et al.			
	US 2001/0002731 A1	06/07/2001	Ueda			
	US 2001/0003064 A1	06/07/2001	Ohto			

**FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

			J. Yota et al., "Comparison Between HDP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 76-78, June 5-7, 2000.

EXAMINER

DATE CONSIDERED

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